

Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS L2	650	multi adj layer adj wiring adj board	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/11 14:18
2	BRS L3	95	(((((wiring or conductor or line or interconnect\$6 or pattern) near4 (inside or within or embedded) near4 (SiO or "silicon dioxide" or insulation or insulating or insulator)) same (element or die or dies or dice or chip or device)) and ((@ad<20000113) or (@rlad<20000113))) and (second!)) and (vias or through-hole or "through hole" or via or aperture or hole or opening)) and multi-layer\$4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/11 14:19
3	BRS L4	132	((257/686,698,700).CCLS.) and ((semiconductor near2 (chip or element or device or dice or die))) and ((multi-layer\$6 or multilayer\$6) near2 board)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/11 14:19

	Type	L #	Hits	Search Text	DBs	Time Stamp
4	BRS	L5	332	(semiconductor chip or chip) and (multi adj layer adj wiring adj board)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/11 14:25

	Type	Hits	Search Text	DBs	Time Stamp
1	IS&R	3749	(257/686,698,700).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/20 16:21
2	BRS	583	multi adj layer adj wiring adj board	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/20 16:21
3	BRS	292	(semiconductor chip or chip) and (multi adj layer adj wiring adj board)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/20 16:22
4	BRS	684657	(semiconductor near2 (chip or element or device or dice or die))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/20 16:22
5	BRS	18681	(multi-layer\$6 or multilayer\$6) near2 board	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/20 16:23
6	BRS	117	((257/686,698,700).CCLS.) and ((semiconductor near2 (chip or element or device or dice or die))) and ((multi-layer\$6 or multilayer\$6) near2 board)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/20 16:23
7	IS&R	1192	(257/698).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/20 16:31
8	BRS	116	(multi adj layer adj wiring adj board) same (semiconductor adj element or chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/20 16:47
9	BRS	794	((257/686).CCLS.) and (@ad<20000113)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/20 16:48
10	IS&R	1415	(257/700).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/20 17:43
11	IS&R	1150	(257/734).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/20 18:24

	Type	Hits	Search Text	DBs	Time Stamp
12	IS&R	168	(257/736).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/20 18:44
13	IS&R	159	(257/748).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/20 18:59
14	IS&R	1431	(257/686).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/20 19:43
15	BRS	8542	((wiring or conductor or line or interconnect\$6 or pattern) near4 (inside or within or embedded) near4 (SiO or "silicon dioxide" or insulation or insulating or insulator))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 12:52
16	BRS	9862256	element or die or dies or dice or chip or device	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 12:53
17	BRS	2579	((wiring or conductor or line or interconnect\$6 or pattern) near4 (inside or within or embedded) near4 (SiO or "silicon dioxide" or insulation or insulating or insulator)) same (element or die or dies or dice or chip or device)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 12:53
18	BRS	1555	((wiring or conductor or line or interconnect\$6 or pattern) near4 (inside or within or embedded) near4 (SiO or "silicon dioxide" or insulation or insulating or insulator)) same (element or die or dies or dice or chip or device)) and ((@ad<20000113) or (@rlad<20000113))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 12:54

	Type	Hits	Search Text	DBs	Time Stamp
19	BRS	1035	(((((wiring or conductor or line or interconnect\$6 or pattern) near4 (inside or within or embedded) near4 (SiO or "silicon dioxide" or insulation or insulating or insulator)) same (element or die or dies or dice or chip or device)) and (@ad<20000113) or (@rlad<20000113))) and (second!))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 12:54
20	BRS	907	(((((wiring or conductor or line or interconnect\$6 or pattern) near4 (inside or within or embedded) near4 (SiO or "silicon dioxide" or insulation or insulating or insulator)) same (element or die or dies or dice or chip or device)) and (@ad<20000113) or (@rlad<20000113))) and (second!)) and (vias or through-hole or "through hole" or via or aperture or hole or opening)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 12:55
21	BRS	95	(((((wiring or conductor or line or interconnect\$6 or pattern) near4 (inside or within or embedded) near4 (SiO or "silicon dioxide" or insulation or insulating or insulator)) same (element or die or dies or dice or chip or device)) and (@ad<20000113) or (@rlad<20000113))) and (second!)) and (vias or through-hole or "through hole" or via or aperture or hole or opening)) and multi-layer\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 15:35